



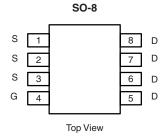
P-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)		
	0.0105 at V _{GS} = - 10 V	- 12.6		
- 30	0.0125 at V _{GS} = - 4.5 V	- 11.5		
	0.0195 at V _{GS} = - 2.5 V	- 9.2		

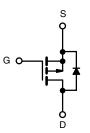
FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFETs
- Compliant to RoHS Directive 2002/95/EC





Ordering Information: Si4427BDY-T1-E3 (Lead (Pb)-free) Si4427BDY-T1-GE3 (Lead (Pb)-free and Halogen-free)



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted						
Parameter		Symbol	10 s	Steady State	Unit	
Drain-Source Voltage		V _{DS}	- 30		V	
Gate-Source Voltage		V _{GS}	± 12			
Continuous Drain Current /T 150 °C\8	T _A = 25 °C	- I _D	- 12.6	- 9.7		
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C		- 10.1	- 7.7		
Pulsed Drain Current		I _{DM}	- 50		Α	
Continuous Source Current (Diode Conduction) ^a		I _S	- 2.5	- 1.3		
Mariana Barra Birata di ad	T _A = 25 °C	P _D	2.5	1.5	W	
Maximum Power Dissipation ^a	T _A = 70 °C	T D	1.6	0.9		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Marrian Installanta Ambienta	t ≤ 10 s	R _{thJA}	40	50	
Maximum Junction-to-Ambient ^a	Steady State	¹ ¹thJA	70	85	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	15	18	

a. Surface Mounted on 1" x 1" FR4 board.

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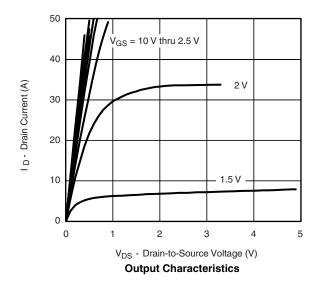
Parameter	Symbol	Test Conditions Min.		Тур.	Max.	Unit	
Static				•			
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 0.60		- 1.4	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$			± 100	nA	
Zero Gate Voltage Drain Current		V _{DS} = - 30 V, V _{GS} = 0 V	- 1				
	I _{DSS}	V _{DS} = - 30 V, V _{GS} = 0 V, T _J = 55 °C			- 5	μΑ	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le -5 \text{ V}, V_{GS} = -10 \text{ V}$	- 50			Α	
		V _{GS} = - 10 V, I _D = - 12.6 A		0.0088	0.0105	Ω	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 4.5 V, I _D = - 11.5 A		0.0105	0.0125		
		V _{GS} = - 2.5 V, I _D = - 5.1 A		0.0150	0.0195		
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 15 V, I _D = - 12.6 A		44		S	
Diode Forward Voltage ^a	V_{SD}	I _S = - 2.5 A, V _{GS} = 0 V		- 0.8	- 1.2	V	
Dynamic ^b							
Total Gate Charge	Q_g			47.2	70		
Gate-Source Charge	Q _{gs}	V _{DS} = - 15 V, V _{GS} = - 4.5 V, I _D = - 12.6 A		9.5		nC	
Gate-Drain Charge	Q_{gd}			16.6		1	
Turn-On Delay Time	t _{d(on)}			12	20		
Rise Time	t _r	V_{DD} = - 15 V, R_L = 15 Ω		15	25]	
Turn-Off Delay Time	t _{d(off)}	$I_D \cong$ - 1 A, V_{GEN} = - 10 V, R_g = 6 Ω		242	360	ns	
Fall Time	t _f			110	165		
Source-Drain Reverse Recovery Time	t _{rr}	I _F = - 2.5 A, dl/dt = 100 A/μs		70	110		

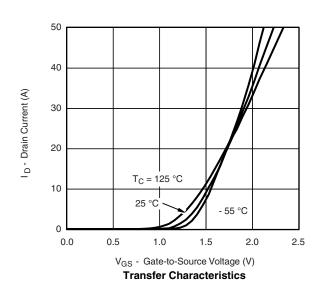
Notes:

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



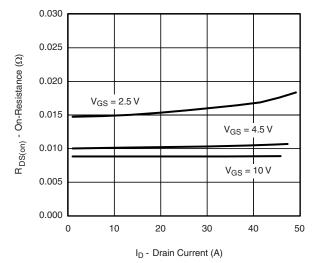




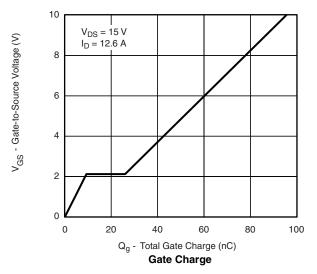


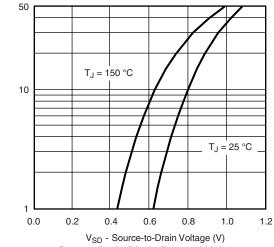


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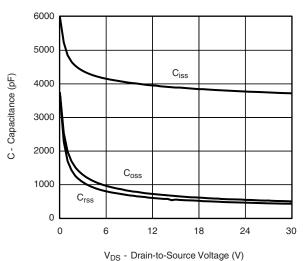


On-Resistance vs. Drain Current



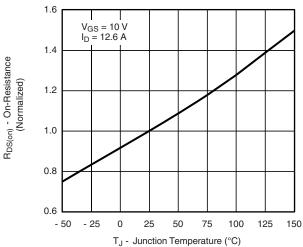


Source-Drain Diode Forward Voltage

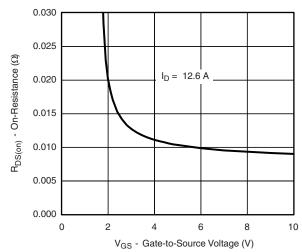


Capacitance





On-Resistance vs. Junction Temperature



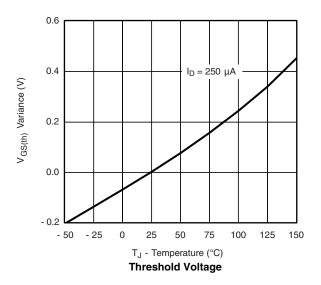
On-Resistance vs. Gate-to-Source Voltage

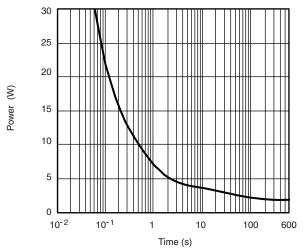
I_S - Source Current (A)

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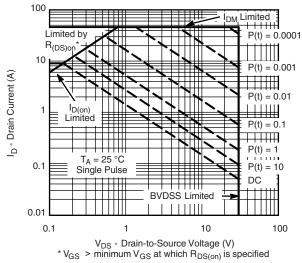
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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

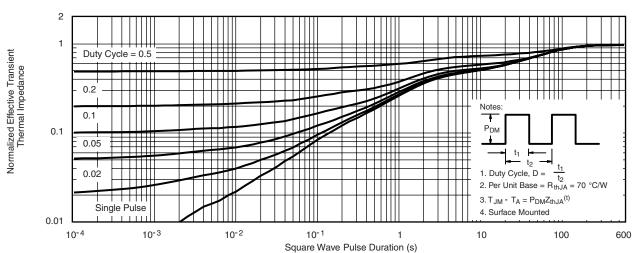




Single Pulse Power, Junction-to-Ambient



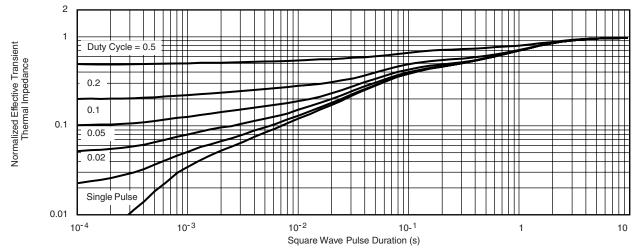




Normalized Thermal Transient Impedance, Junction-to-Ambient



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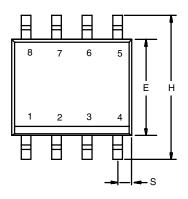


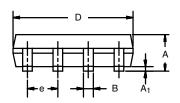
Normalized Thermal Transient Impedance, Junction-to-Foot

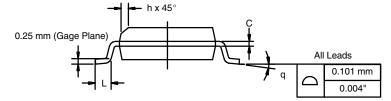
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SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012







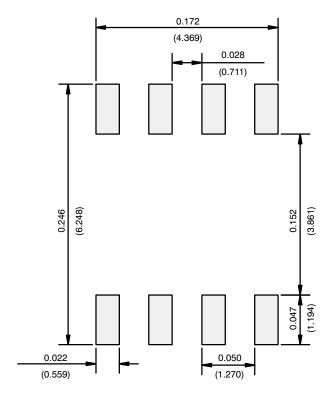
	MILLIMETERS INCHES			HES		
DIM	Min	Max	Min	Max		
Α	1.35	1.75	0.053	0.069		
A ₁	0.10	0.20	0.004	0.008		
В	0.35	0.51	0.014	0.020		
С	0.19	0.25	0.0075	0.010		
D	4.80	5.00	0.189	0.196		
Е	3.80	4.00	0.150	0.157		
е	1.27	BSC	0.050 BSC			
Н	5.80	6.20	0.228	0.244		
h	0.25	0.50	0.010	0.020		
L	0.50	0.93	0.020	0.037		
q	0°	8°	0°	8°		
S	0.44	0.64	0.018	0.026		
ECN: C-06527-Rev. I. 11-Sep-06						

DWG: 5498

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RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads Dimensions in Inches/(mm)

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